

Measurement of the density of gap states in hydrogenated charge spectroscopy

Physical Review B

25, 5285-5320

DOI: [10.1103/physrevb.25.5285](https://doi.org/10.1103/physrevb.25.5285)

Citation Report

#	ARTICLE	IF	CITATIONS
1	Transport and recombination in hydrogenated amorphous silicon. , 1984, , 133-161.		3
2	Calculation of the dynamic response of Schottky barriers with a continuous distribution of gap states. Physical Review B, 1982, 25, 5321-5350.	1.1	228
3	Amorphous solid and bipolaronic ground-state. Solar Energy Materials and Solar Cells, 1982, 8, 71-79.	0.4	1
4	States in the gap of amorphous hydrogenated silicon. Solar Energy Materials and Solar Cells, 1982, 8, 269-276.	0.4	9
5	Recombination centers in phosphorous doped hydrogenated amorphous silicon. Solid State Communications, 1982, 44, 1423-1426.	0.9	116
6	The correlation energy of the dangling silicon bond in a α -Si:H. Solid State Communications, 1982, 44, 477-480.	0.9	107
7	Admittance of semiconductor junctions with gap states having a continuous distribution in energy. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1983, 2, 1561-1581.	0.4	0
9	The electronic properties of dangling bonds in silicon. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 116, 79-84.	0.9	2
10	Study of gap states density in A-Si: H using thermally stimulated current in a space charge zone. Solid State Communications, 1983, 48, 79-83.	0.9	14
11	On the intensity dependence of the photoconductivity in a-Si:H. Solid State Communications, 1983, 47, 107-110.	0.9	12
12	Photo-induced changes in the bulk density of gap states in hydrogenated amorphous silicon associated with the Staebler-Wronski effect. Solar Cells, 1983, 9, 119-131.	0.6	24
13	Optical absorption spectra of surface or interface states in hydrogenated amorphous silicon. Applied Physics Letters, 1983, 42, 105-107.	1.5	121
14	Space charge limited currents: Refinements in analysis and applications to α -Si \times Gex: H alloys. Journal of Applied Physics, 1983, 54, 6401-6416.	1.1	94
15	Electronic structure of amorphous semiconductors. Advances in Physics, 1983, 32, 361-452.	35.9	150
16	Theory of electron-hole kinetics in amorphous semiconductors under illumination: Application to solar cells. Journal of Applied Physics, 1983, 54, 3951-3957.	1.1	7
17	Effects of doping on transport and deep trapping in hydrogenated amorphous silicon. Applied Physics Letters, 1983, 43, 672-674.	1.5	228
18	Modeling of thin film solar cells: Uniform field approximation. Journal of Applied Physics, 1983, 54, 7176-7186.	1.1	197
19	Space charge spectroscopy of the gap states in hydrogenated amorphous silicon counterdoped with boron. Journal of Non-Crystalline Solids, 1983, 59-60, 261-264.	1.5	12

#	ARTICLE	IF	CITATIONS
20	Deep-level distributions in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1983, 59-60, 265-268.	1.5	26
21	Frequency and temperature dependence of the space charge capacitance in a-Si:H films. Journal of Non-Crystalline Solids, 1983, 59-60, 269-272.	1.5	14
22	Application of a new capacitance-voltage method to a-Si:H. Journal of Non-Crystalline Solids, 1983, 59-60, 277-280.	1.5	6
23	Comparison of the density of gap states in a-Si:H found by different methods. Journal of Non-Crystalline Solids, 1983, 59-60, 293-296.	1.5	18
24	High-temperature kink of the conductivity of doped a-Si:H films. Journal of Non-Crystalline Solids, 1983, 59-60, 301-304.	1.5	9
25	The incorporation of phosphorus in amorphous silicon. Journal of Non-Crystalline Solids, 1983, 59-60, 613-616.	1.5	9
26	Isothermal Photocurrent Transient Spectroscopy of Gap States in Amorphous Chalcogenide Semiconductors. Japanese Journal of Applied Physics, 1983, 22, 1818-1821.	0.8	6
27	Dopant states in a-Si: H. III. Triply coordinated boron. Physical Review B, 1983, 28, 4666-4670.	1.1	19
28	Measurement of deep levels in hydrogenated amorphous silicon by transient voltage spectroscopy. Applied Physics Letters, 1983, 42, 981-983.	1.5	46
29	Energy dependence of the carrier mobility-lifetime product in hydrogenated amorphous silicon. Physical Review B, 1983, 27, 4861-4871.	1.1	49
30	Study of gap states in hydrogenated amorphous silicon by transient and steady-state photoconductivity measurements. Physical Review B, 1983, 27, 7460-7465.	1.1	78
31	Dopant states in a-Si: H. I. Tight-binding-model results. Physical Review B, 1983, 28, 4647-4657.	1.1	31
32	Temperature dependence of electron-capture cross section of localized states in a-Si:H. Physical Review B, 1983, 27, 5184-5187.	1.1	54
33	Capacitance temperature analysis of midgap states in hydrogenated amorphous silicon. Journal of Applied Physics, 1983, 54, 4001-4007.	1.1	26
34	A theory of the admittance of an amorphous silicon Schottky barrier. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1983, 48, 111-125.	0.6	34
35	Optoelectrical properties of amorphous-crystalline silicon heterojunctions. Applied Physics Letters, 1984, 45, 452-454.	1.5	25
36	ac field effect in amorphous silicon. Journal of Applied Physics, 1984, 56, 572-574.	1.1	0
37	Characterization of CdS/CdTe thin-film solar cells by admittance spectroscopy and deep-level transient spectroscopy. Journal of Applied Physics, 1984, 56, 3508-3517.	1.1	31

#	ARTICLE	IF	CITATIONS
38	Electrical properties of amorphous/crystalline silicon heterojunctions. Journal of Applied Physics, 1984, 55, 1012-1019.	1.1	275
39	Annealing of CdS/CdTe solar cells. Journal of Applied Physics, 1984, 55, 3190-3192.	1.1	3
40	Recombination in a-Si: H: Transitions through defect states. Physical Review B, 1984, 30, 5861-5870.	1.1	101
41	Localized density of states in amorphous silicon determined by electrophotography. Applied Physics Letters, 1984, 45, 438-439.	1.5	10
42	Localized states in compensated a-Si:H. Physical Review B, 1984, 29, 2331-2333.	1.1	59
43	The relationship between space-charge-limited current and density of states in amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1984, 50, 11-21.	0.6	27
44	Chapter 11 Schottky Barriers on a-Si: H. Semiconductors and Semimetals, 1984, 21, 375-406.	0.4	8
45	Chapter 8 Doping Effects in a-Si: H. Semiconductors and Semimetals, 1984, , 257-307.	0.4	27
46	A DLTS study of the effects of boron counterdoping on the gap states in n-type hydrogenated amorphous silicon. Solid State Communications, 1984, 50, 991-994.	0.9	3
47	Conductivity and thermoelectric power below a mobility edge in amorphous silicon. Solid State Communications, 1984, 51, 569-572.	0.9	3
48	On the measurement of densities of states in amorphous semiconductors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1984, 49, L57-L59.	0.6	13
49	Si(Li) X-Ray Detectors with Amorphous Silicon Passivation. IEEE Transactions on Nuclear Science, 1984, 31, 331-335.	1.2	16
50	Charge transient and optical absorption measurements of characteristic gap states in phosphorus doped a-Si:H. Journal of Non-Crystalline Solids, 1984, 68, 147-152.	1.5	12
51	Doping effects in amorphous silicon. Journal of Non-Crystalline Solids, 1984, 66, 1-12.	1.5	19
52	Intrinsic stress measurements as a quantitative measure of the growth morphology transition in a-Si:H. Journal of Non-Crystalline Solids, 1984, 66, 87-92.	1.5	12
53	New paramagnetic states in amorphous silicon and germanium. Journal of Non-Crystalline Solids, 1984, 66, 145-150.	1.5	15
54	Defect states and carrier capture processes in a-Si:H. Journal of Non-Crystalline Solids, 1984, 66, 205-216.	1.5	26
55	Thermostimulated currents in a-Si:H and a-Si:N:H. Journal of Non-Crystalline Solids, 1984, 66, 231-236.	1.5	5

#	ARTICLE	IF	CITATIONS
56	Charge transfer doping in amorphous semiconductor superlattices. Applied Physics Letters, 1984, 45, 179-181.	1.5	71
57	Effect of silane dilution on intrinsic stress in glow discharge hydrogenated amorphous silicon films. Journal of Applied Physics, 1984, 55, 946-951.	1.1	81
58	Chapter 2 Density of States from Junction Measurements in Hydrogenated Amorphous Silicon. Semiconductors and Semimetals, 1984, 21, 9-98.	0.4	47
59	Accurate determination of the free carrier capture kinetics of deep traps by space-charge methods. Journal of Applied Physics, 1984, 55, 3644-3657.	1.1	165
60	Material Properties Controlling the Performance of Amorphous Silicon Thin Film Transistors. Materials Research Society Symposia Proceedings, 1984, 33, 259.	0.1	33
61	Doping and gap states in amorphous silicon. Journal of Physics C: Solid State Physics, 1984, 17, L349-L354.	1.5	23
62	On the analysis of space-charge-limited current-voltage characteristics and the density of states in amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1984, 49, L1-L7.	0.6	9
63	Studies of the frequency-dependent admittances of Schottky barriers formed on sputtered hydrogenated amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1984, 49, 565-595.	0.6	30
64	Measurements of the electron density in n-type a-Si: H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1984, 50, L19-L22.	0.6	51
65	Study of light-induced metastable defects by means of temperature-modulated space-charge-limited currents. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 52, L25-L30.	0.6	27
66	Defect States in Silicon Nitride. Materials Research Society Symposia Proceedings, 1985, 49, 215.	0.1	12
67	Capacitance Studies of Light-Induced Effects in Undoped Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1985, 49, 311.	0.1	4
68	Transient Photoconductivity Studies of a-Si:H Interfaces. Materials Research Society Symposia Proceedings, 1985, 49, 79.	0.1	4
69	Effect of hydrogenation on the conductivity of UHV-deposited amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 51, 55-66.	0.6	18
70	Gap states in phosphorus-doped amorphous silicon studied by isothermal capacitance transient spectroscopy. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 52, 33-57.	0.6	90
71	Amorphes Silizium (a-Si). Physik in Unserer Zeit, 1985, 16, 50-62.	0.0	12
72	A new model for ac conduction in disordered solids. Physica Status Solidi A, 1985, 88, 315-323.	1.7	17
73	Thermally stimulated current studies of the density of gap states in amorphous silicon. Solid State Communications, 1985, 55, 147-150.	0.9	10

#	ARTICLE	IF	CITATIONS
74	Boron doping of amorphous hydrogenated silicon films prepared by r.f. sputtering. Thin Solid Films, 1985, 124, 49-53.	0.8	2
75	Defects in amorphous semiconductors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 51, 183-192.	0.6	19
76	Dopant and defect states in a-Si:H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 52, 235-245.	0.6	50
77	Analysis of thermally stimulated currents in amorphous silicon. Physical Review B, 1985, 32, 4052-4059.	1.1	5
78	Admittance frequency dependence of Schottky barriers formed on dc triode sputtered amorphous silicon: Hydrogen influence on deep gap state characteristics. Journal of Applied Physics, 1985, 58, 1292-1301.	1.1	19
79	Effects of dopants and defects on light-induced metastable states in a-Si:H. Physical Review B, 1985, 31, 2263-2269.	1.1	81
80	Identification of deep-gap states in a-Si:H by photo-depopulation-induced electron-spin resonance. Physical Review B, 1985, 31, 4066-4069.	1.1	46
81	Determination of distribution of states in hydrogenated amorphous silicon from capacitance-voltage characteristics. Journal of Applied Physics, 1985, 58, 2617-2627.	1.1	26
82	The electrical characterization of surfaces, interfaces and contacts to a-Si:H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 51, 1-17.	0.6	49
83	Transient conductivity and photoconductivity in a-Si:H. Physical Review B, 1985, 32, 3910-3920.	1.1	22
84	Doping mechanism in a-Si:H. Physical Review B, 1985, 31, 3817-3821.	1.1	33
85	Energy dependence of the optical matrix element in hydrogenated amorphous and crystalline silicon. Physical Review B, 1985, 31, 5187-5198.	1.1	297
86	On the electrical methods for the measurement of the density of localized states in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1985, 76, 215-242.	1.5	16
87	Defects and associated electronic states in amorphous semiconductors. Journal of Non-Crystalline Solids, 1985, 71, 113-123.	1.5	13
88	Localized states in doped amorphous silicon. Journal of Non-Crystalline Solids, 1985, 77-78, 1-16.	1.5	154
89	Density-of-states distribution in the mobility gap of a-Si:H. Journal of Non-Crystalline Solids, 1985, 77-78, 273-280.	1.5	44
90	Implications of recent density-of-states measurements for optical and transport properties of a-Si:H. Journal of Non-Crystalline Solids, 1985, 77-78, 281-290.	1.5	26
91	Correlation of optical and thermal emission from mobility GAP states in doped hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1985, 77-78, 291-294.	1.5	8

#	ARTICLE	IF	CITATIONS
92	Amplitude and phase of transient AC photocurrent of a-Si:H pin+ diode under infrared illumination. Journal of Non-Crystalline Solids, 1985, 77-78, 315-318.	1.5	0
93	Energy placement of the D ⁺ dangling-bond transition in a-Si:H from phot capacitance and photocurrent spectroscopies. Journal of Non-Crystalline Solids, 1985, 77-78, 335-338.	1.5	8
94	The density of localised states relevant to different properties of inhomogeneous amorphous semiconductors. Journal of Non-Crystalline Solids, 1985, 77-78, 351-354.	1.5	2
95	Internal photoemission transient current temperature spectroscopy – a new method for determination of the gap state distribution in a-Si:H. Journal of Non-Crystalline Solids, 1985, 77-78, 355-358.	1.5	2
96	Electrophotographic spectroscopy of gap states in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1985, 77-78, 359-362.	1.5	5
97	Capacitance studies of light induced effects in undoped a-Si:H. Journal of Non-Crystalline Solids, 1985, 77-78, 381-384.	1.5	5
98	On the auto-compensation mechanism in amorphous silicon. Journal of Non-Crystalline Solids, 1985, 77-78, 435-438.	1.5	3
99	Trap parameters in undoped sputtered a-Si:H from TSC. Journal of Non-Crystalline Solids, 1985, 77-78, 683-686.	1.5	2
100	Drive-level capacitance profiling: Its application to determining gap state densities in hydrogenated amorphous silicon films. Applied Physics Letters, 1985, 47, 412-414.	1.5	163
101	Recombination at dangling bonds and steady-state photoconductivity in a-Si:H. Physical Review B, 1986, 34, 4088-4098.	1.1	92
102	Assessment of lattice relaxation effects in transitions from mobility gap states in hydrogenated amorphous silicon using transient phot capacitance techniques. Applied Physics Letters, 1986, 49, 722-724.	1.5	60
103	Transient electronic response in hydrogenated amorphous silicon. Journal of Applied Physics, 1986, 59, 3503-3507.	1.1	10
104	DOPANT AND DEFECT STATES IN AMORPHOUS SILICON. , 1986, , 278-288.		0
105	The energy of the dangling-bond states in a-Si. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 53, L1-L7.	0.6	73
106	More theory of the admittance of an amorphous silicon Schottky barrier. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 54, 421-438.	0.6	29
107	Level of dangling-bond centres in a-Si: H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 54, L119-L123.	0.6	10
108	The transient photoconductivity of inhomogeneous amorphous semiconductors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 53, 497-507.	0.6	4
109	Back-To-Back Amorphous Silicon Diodes For Driving Lc Displays. Materials Research Society Symposia Proceedings, 1986, 70, 663.	0.1	1

#	ARTICLE	IF	CITATIONS
110	Study of Trapping and Recombination In a-Si:H By Means of Infrared Enhancement Spectra of Photoconductivity. Materials Research Society Symposia Proceedings, 1986, 70, 131.	0.1	3
111	Interpretation of The a-Si:H DLTS and ICTS Experimental Data. Materials Research Society Symposia Proceedings, 1986, 70, 161.	0.1	1
112	Capacitance-Voltage Characteristics of Metallic Gate/Oxide/a-Si:H Mos Structures. Materials Research Society Symposia Proceedings, 1986, 70, 167.	0.1	4
113	Validity of quasi-static capacitance-voltage measurements applied to hydrogenated amorphous silicon diodes. Applied Physics A: Solids and Surfaces, 1986, 40, 171-176.	1.4	3
114	Functional integral approach to positionally disordered systems. Physical Review B, 1986, 33, 5482-5488.	1.1	3
115	Substitutional doping of amorphous silicon a comparison of different doping mechanisms. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 53, 257-268.	0.6	28
116	Origin of the non-exponential photocurrent decay in amorphous semiconductors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 54, 285-299.	0.6	22
117	Amorphous silicon p-n junction diodes. Applied Physics Letters, 1986, 48, 1006-1008.	1.5	9
118	Density of midgap states and Urbach edge in chemically vapor deposited hydrogenated amorphous silicon films. Journal of Applied Physics, 1986, 60, 1046-1054.	1.1	11
119	The localized density of states in amorphous silicon determined by electrophotography. Journal of Applied Physics, 1986, 60, 3176-3181.	1.1	8
120	Measurement of deep states in undoped amorphous silicon by current transient spectroscopy. Journal of Applied Physics, 1986, 59, 4079-4086.	1.1	26
121	Energy levels of dangling-bond centres in a-Si:H studied by photocapadntance transient spectroscopy. Philosophical Magazine Letters, 1987, 55, 135-141.	0.5	11
122	Electron Relaxation Properties and Transient Spectroscopy of Hydrogenated Amorphous Silicon. Japanese Journal of Applied Physics, 1987, 26, 524-530.	0.8	4
123	Photoinduced Absorption on Phosphorus and Nitrogen Doped a-Si:H Films Prepared at High Deposition-Rate. Japanese Journal of Applied Physics, 1987, 26, 655-659.	0.8	0
124	Photocapacitance characteristics of amorphous silicon Schottky diode sensor arrays and their changes due to the Staebler-Wronski effect. Journal of Applied Physics, 1987, 61, 585-590.	1.1	2
125	Thermal-equilibrium processes in amorphous silicon. Physical Review B, 1987, 35, 1316-1333.	1.1	326
126	Detailed investigation of doping in hydrogenated amorphous silicon and germanium. Physical Review B, 1987, 35, 5666-5701.	1.1	273
127	Observtion of an oxygen-related mobility-gap defect in ion-implanted hydrogenated amorphous silicon films. Physical Review B, 1987, 35, 4141-4144.	1.1	9

#	ARTICLE	IF	CITATIONS
128	Determination of gap state density distribution in hydrogenated amorphous silicon from light-induced effects. Journal of Applied Physics, 1987, 62, 1514-1516.	1.1	3
129	Space-charge-limited current diode model for amorphous silicon solar cells and their degradation. Journal of Applied Physics, 1987, 61, 5458-5466.	1.1	10
130	The Role of Lattice Relaxation in the Competition Between Optical and Thermal Transitions from Gap States in Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1987, 95, 33.	0.1	0
131	States in the Gap of Doped and Undoped a-Si:H Studied by Photomodulation Spectroscopy. Materials Research Society Symposia Proceedings, 1987, 95, 51.	0.1	1
132	Capacitance Studies of Ion-Implanted N-Type Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1987, 95, 71.	0.1	0
133	Experimental determination of the density of gap states in amorphous silicon by Schottky barrier admittance. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1987, 56, 429-441.	0.6	6
134	Percolative transport in amorphous semiconductors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1987, 56, 861-871.	0.6	2
135	The density of states of sputtered a-Si:H studied by the space-charge-limited current technique The influence of deposition parameters, light and keV-electron irradiation. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1987, 56, 321-333.	0.6	17
136	The density of states in undoped and doped amorphous hydrogenated silicon. Journal of Non-Crystalline Solids, 1987, 90, 91-98.	1.5	56
137	Optical transitions involving deep levels in amorphous semiconductors. Journal of Non-Crystalline Solids, 1987, 97-98, 527-530.	1.5	0
138	Transient photoconductivity studies in a-Si:H. Journal of Non-Crystalline Solids, 1987, 97-98, 599-602.	1.5	3
139	a-Si:H gap states investigated by CPM and SCLC. Journal of Non-Crystalline Solids, 1987, 97-98, 715-722.	1.5	57
140	Energy level of neutral dangling-bond center (DO) in undoped a-Si:H determined by isothermal capacitance transient spectroscopy under high temperature. Journal of Non-Crystalline Solids, 1987, 97-98, 723-726.	1.5	4
141	Capacitance studies of ion-implanted n-type hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1987, 97-98, 763-766.	1.5	0
142	Instability of gap states in phosphorus doped a-Si:H, demonstrated in DLTS. Journal of Non-Crystalline Solids, 1987, 97-98, 815-818.	1.5	0
143	Defect formation in amorphous silicon doping superlattice films. Journal of Non-Crystalline Solids, 1987, 97-98, 875-878.	1.5	1
144	Doping efficiency in r.f.-sputtered hydrogenated amorphous silicon. Philosophical Magazine Letters, 1987, 55, 41-46.	0.5	6
145	Measurement of heterojunction band offsets by admittance spectroscopy: InP/Ga _{0.47} In _{0.53} As. Applied Physics Letters, 1987, 50, 736-738.	1.5	140

#	ARTICLE	IF	CITATIONS
146	Transition from diffusive to ballistic capture related to hydrogen incorporation in amorphous silicon. Philosophical Magazine Letters, 1987, 55, 63-68.	0.5	4
147	An anomalous feature on the DLTS spectrum of silicon. Solid State Communications, 1987, 62, 719-722.	0.9	4
148	On the zero temperature statistics for the density of gap states of hydrogenated amorphous silicon. Solid State Communications, 1987, 64, 583-584.	0.9	1
149	Amorphous semiconductor-electrolyte junction. Journal of Electroanalytical Chemistry and Interfacial Electrochemistry, 1987, 228, 119-134.	0.3	34
150	Phase shift analysis of modulated photocurrent: Determination of the energy scale. Applied Physics A: Solids and Surfaces, 1988, 45, 221-224.	1.4	1
151	Energy levels of gap states in a-Si:H. Solid State Communications, 1988, 68, 155-158.	0.9	6
152	Frequency resolved EBIC measurements for determination of the density of localized states in a-Si:H. Solid State Communications, 1988, 67, 557-560.	0.9	4
153	Junction capacitance studies of deep defects in undoped hydrogenated amorphous silicon. Solar Cells, 1988, 24, 287-297.	0.6	5
154	The density of states in the mobility gap of amorphous-silicon films computed by a new analytical method. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1988, 10, 237-246.	0.4	0
155	Capacitance characterisation of Cu ₂ S/CdS heterojunctions. Semiconductor Science and Technology, 1988, 3, 781-785.	1.0	14
156	Interband optical absorption in amorphous silicon. Journal of Non-Crystalline Solids, 1988, 103, 234-249.	1.5	29
157	Defect levels in CdS/CuInSe ₂ film solar cells. Journal of Applied Physics, 1988, 63, 1203-1206.	1.1	6
158	Transient photocapacitance and photocurrent studies of undoped hydrogenated amorphous silicon. Applied Physics Letters, 1988, 53, 403-405.	1.5	55
159	Noise spectroscopy of deep level (DX) centers in GaAs _{1-x} Al _x Ga _{1-x} As heterostructures. Journal of Applied Physics, 1988, 63, 1541-1548.	1.1	90
160	Evidence of $\sigma = 2.013$ defect centers in a-Si:H. Physical Review B, 1988, 37, 4886-4892.	1.1	0
161	Mechanisms of thermal equilibration in doped amorphous silicon. Physical Review B, 1988, 37, 4209-4224.	1.1	166
162	Distribution of occupied near-surface band-gap states in a-Si:H. Physical Review B, 1988, 38, 7680-7693.	1.1	82
163	Exponential Conduction-Band Tail in P-Doped a-Si:H. Physical Review Letters, 1988, 60, 2697-2700.	2.9	46

#	ARTICLE	IF	CITATIONS
164	A critical analysis of the determination of the density of defects in a-Si/sub 1-x/Ge/sub x/ alloys with the PDS technique. , 1988, , .		0
165	A novel method for determining the gap state profile and its application to amorphous Si _{1-x} Ge _x : H films. Journal of Applied Physics, 1988, 64, 1964-1973.	1.1	56
166	High-temperature light-induced effects in hydrogenated amorphous silicon. Physical Review B, 1988, 38, 13453-13455.	1.1	2
167	Evaluation of Deep States in Amorphous-Silicon/Silicon-Nitride System from Charge-Coupled Device Characteristics. Japanese Journal of Applied Physics, 1988, 27, L1337-L1339.	0.8	2
168	Density-of-State Distribution for Undoped a-Si:H and a-Si _{1-x} Ge _x :H Determined by Transient Heterojunction-Monitored Capacitance Method. Japanese Journal of Applied Physics, 1988, 27, L516-L518.	0.8	3
169	Gap states in undoped amorphous silicon studied by below-gap modulated photocurrent spectroscopy. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1988, 58, 171-184.	0.6	21
170	Flicker noise in hydrogenated amorphous-silicon Schottky diodes. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1988, 57, 259-269.	0.6	4
171	Optical-bias-enhanced transient photocurrent in amorphous silicon. Physical Review B, 1989, 40, 9652-9660.	1.1	16
172	State distribution and ambipolar diffusion length in n-type hydrogenated amorphous silicon. Journal of Applied Physics, 1989, 66, 215-218.	1.1	5
173	Spatially resolved and energy-resolved defect kinetics in a-Si:H: A comprehensive study by phase-shift analysis of modulated photocurrents. Physical Review B, 1989, 39, 5311-5326.	1.1	76
174	Dangling bonds in doped amorphous silicon: Equilibrium, relaxation, and transition energies. Physical Review B, 1989, 39, 5107-5115.	1.1	47
175	Urbach tail and gap state distribution in as-deposited and annealed a-(C-Si-Ge): H alloys. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1989, 60, 713-720.	0.6	2
176	Comparative properties of systems involving dangling bonds. Radiation Effects and Defects in Solids, 1989, 111-112, 211-219.	0.4	0
177	Analysis of Weighting Function in Transient Spectroscopy for Precise Measurement of Deep States. Japanese Journal of Applied Physics, 1989, 28, 39-45.	0.8	9
178	Origin and nature of gap states in a-Si:H alloys. Solid State Communications, 1989, 69, 681-684.	0.9	6
179	Theoretical investigation of the C-V relationship for an amorphous silicon p-n junction. Solid-State Electronics, 1989, 32, 727-731.	0.8	1
180	Sensitivity analysis of the modulated photocurrent method. Applied Physics A: Solids and Surfaces, 1989, 48, 237-240.	1.4	2
181	Band offsets and deep defect distribution in hydrogenated amorphous silicon/crystalline silicon heterostructures. Applied Physics Letters, 1989, 55, 1232-1234.	1.5	52

#	ARTICLE	IF	CITATIONS
182	Oxygen traps in evaporated hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1989, 107, 301-308.	1.5	2
183	Capacitance studies of deep defects in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1989, 114, 381-386.	1.5	5
184	A new treatment of Schottky barrier capacitance-voltage characteristics: Discussion of usual assumptions and determination of the deep gap states density in a-Si _{1-x} Ge _x :H alloys. Journal of Non-Crystalline Solids, 1989, 114, 432-434.	1.5	24
185	Optical absorption spectra in a-Si:H measured by PDS and CPM in situ. Journal of Non-Crystalline Solids, 1989, 114, 438-440.	1.5	2
186	Evolution of the density of states profile above midgap in a-SiGe:H alloys from complementary transport measurements. Journal of Non-Crystalline Solids, 1989, 114, 534-536.	1.5	4
187	The carbon impurity dependence of light induced metastable effects in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1989, 114, 603-605.	1.5	4
188	Internal photoemission of holes and the mobility gap of hydrogenated amorphous silicon. Physical Review Letters, 1989, 63, 1420-1423.	2.9	83
189	Role of deep levels and interface states in the capacitance characteristics of all-sputtered CuInSe ₂ /CdS solar cell heterojunctions. Journal of Applied Physics, 1989, 65, 3236-3241.	1.1	13
190	Midgap Defects in a-SiGe:H Devices from Capacitance Measurements. Materials Research Society Symposia Proceedings, 1989, 149, 533.	0.1	1
191	Optical Degradation and Morphology in a-Si:H. Materials Research Society Symposia Proceedings, 1989, 149, 607.	0.1	1
192	Band Offsets and Anomalous Deep Defect Distribution at the Hydrogenated Amorphous Silicon-Crystalline Silicon Interface via Junction Capacitance Techniques. Materials Research Society Symposia Proceedings, 1989, 149, 699.	0.1	2
193	The transport properties of hydrogenated amorphous semiconductors. Springer Tracts in Modern Physics, 1989, , 138-150.	0.1	2
194	Measurement of gap states in undoped a-SiGe: H alloys by modulated photocurrent spectroscopy. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1989, 60, 695-712.	0.6	5
195	Sweep-out measurements of band-tail carriers in a-Si: H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1989, 60, 213-236.	0.6	34
196	Defect creation in the accumulation layer of a-Si: H thin-film transistors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1990, 61, 251-261.	0.6	29
197	The influence of spatially non-uniform density-of-state distributions on the characteristics of a-Si: H thin-film transistors. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1990, 61, 263-276.	0.6	4
198	The Influence of Interfaces on the Gap State Distribution of Undoped a-Si:H. Materials Research Society Symposia Proceedings, 1990, 192, 189.	0.1	6
199	Trace Impurities and Metastable States in a-Si:H. Materials Research Society Symposia Proceedings, 1990, 192, 719.	0.1	1

#	ARTICLE	IF	CITATIONS
200	Capacitance Studies of Metastable States in Light-Soaked, Quench-Cooled, and Bias-Annealed N-Type Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1990, 192, 707.	0.1	5
201	Study of instabilities in amorphous-silicon thin-film transistors by transient current spectroscopy. IEEE Transactions on Electron Devices, 1990, 37, 280-284.	1.6	7
202	Comments on the Meyer-Neldel rule in amorphous semiconductors. Pramana - Journal of Physics, 1990, 34, 561-563.	0.9	0
204	On the Fermi Level Position in a-Si: H(P). Physica Status Solidi (B): Basic Research, 1990, 160, K25.	0.7	3
205	Optical modulation spectroscopy of dangling bonds in a-Si: H. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1990, 61, 393-402.	0.6	20
206	Theory of electrical characteristics for metal-oxide-insulator Schottky barrier and metal-insulator-metal structures. Journal of Applied Physics, 1990, 68, 176-182.	1.1	8
207	Experimental evidence for zero-correlation-energy deep defects in intrinsic hydrogenated amorphous silicon. Physical Review Letters, 1990, 64, 3062-3065.	2.9	21
208	Defect creation by 10-keV electron irradiation in phosphorous-doped a-Si:H. Journal of Applied Physics, 1990, 67, 2800-2805.	1.1	5
209	Characterization of interfaces of metal/amorphized (by implantation) Si/c-Si structures. Journal of Applied Physics, 1990, 67, 1940-1946.	1.1	2
210	Effects of the implantation of oxygen, nitrogen, and carbon on the density of states of n-type hydrogenated amorphous silicon. Physical Review B, 1990, 41, 1529-1541.	1.1	25
211	Density of states determination of amorphous silicon from space-charge-limited photocurrents. Journal of Applied Physics, 1990, 67, 558-560.	1.1	2
212	Study of extrinsic interface states at the Al/Si interface from capacitance-voltage characteristics. International Journal of Electronics, 1990, 68, 69-73.	0.9	0
213	The mobility gaps in a-Si:H and its effects on solar cell performance. , 0, , .		8
214	Direct observation of the silicon nitride on amorphous silicon interface states. Applied Physics Letters, 1990, 56, 940-942.	1.5	16
215	Effect of local structural order on the doping in hydrogenated amorphous silicon (a - Si : H). Journal of Non-Crystalline Solids, 1991, 137-138, 115-118.	1.5	8
216	Density of states spectroscopy in p-type a-Si:H and a-SiC:H. Journal of Non-Crystalline Solids, 1991, 137-138, 311-314.	1.5	0
217	Observation of configuration switching of the D center in a-Si:H. Journal of Non-Crystalline Solids, 1991, 137-138, 319-322.	1.5	16
218	Further study of the determination of the density of gap states by thermally stimulated conductivity. Journal of Non-Crystalline Solids, 1991, 137-138, 355-358.	1.5	10

#	ARTICLE	IF	CITATIONS
219	Similarities and differences in the field-induced doping effect of n-type and of intrinsic a-Si : H. Journal of Non-Crystalline Solids, 1991, 130, 256-259.	1.5	0
220	Lattice Relaxation of Deep Defects in Light-Soaked N-Type Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1991, 219, 39.	0.1	1
221	Density of States Spectroscopy in p-Type a-Si:H and a-SiC:H. Materials Research Society Symposia Proceedings, 1991, 219, 557.	0.1	2
222	An Investigation of Spin and Charge States Associated with Metastable Defects in N-Type Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1991, 219, 569.	0.1	1
223	The Distribution of Occupied Deep Levels in a-Si:H Determined from CPM Spectra. Materials Research Society Symposia Proceedings, 1991, 219, 611.	0.1	8
224	Characterization of Electron Cyclotron Resonance Plasma-Deposited Hydrogenated Amorphous Silicon and Related Alloy Films. Materials Research Society Symposia Proceedings, 1991, 219, 679.	0.1	2
225	Effects of Substrate Parameters on Amorphous-Crystalline Silicon Interface. Materials Research Society Symposia Proceedings, 1991, 219, 819.	0.1	0
226	High-frequency capacitance-voltage characteristics of amorphous (undoped)/crystalline silicon heterostructures. Solid-State Electronics, 1991, 34, 535-543.	0.8	4
227	Experimental studies of the light-induced effects in undoped hydrogenated amorphous silicon as a function of deposition conditions. Thin Solid Films, 1991, 204, 385-395.	0.8	3
228	A model of the small-signal charge DLTS response of traps distributed in both energy and space. Physica Status Solidi A, 1991, 127, 167-177.	1.7	9
229	Deep Level Transient Spectroscopy Study of Staebler-Wronski Effect in a-Si:H. Japanese Journal of Applied Physics, 1991, 30, L243-L245.	0.8	3
230	Enhancement of light-induced degradation in hydrogenated amorphous silicon due to carbon impurities. Applied Physics Letters, 1991, 58, 723-725.	1.5	18
231	Effects of secondary laser illumination during the transient measurement in optical and electrical deep level transient spectroscopy. Applied Physics Letters, 1991, 59, 1861-1863.	1.5	2
232	Gap-state density of lightly P- and B-doped a-Si:H deduced from space-charge-limited photocurrents. Physical Review B, 1991, 43, 4871-4878.	1.1	0
233	Material properties and device evaluations of ECR-deposited a-Si:H and a-SiC:H films. , 0, ,		0
234	Theory of electrical characteristics of a Schottky barrier having exponentially distributed impurity states and metal-insulator-metal structures. Journal of Physics Condensed Matter, 1992, 4, 3507-3515.	0.7	4
235	Effect of Phosphorus Doping and Deposition Temperature on the Deep-Level Transient Spectra in a-Si:H. Japanese Journal of Applied Physics, 1992, 31, L1460-L1462.	0.8	2
236	Observation of a novel relaxation process associated with electronic transitions from deep (D) defects in hydrogenated amorphous silicon. Physical Review Letters, 1992, 69, 3358-3361.	2.9	71

#	ARTICLE	IF	CITATIONS
237	A comprehensive defect model for amorphous silicon. Journal of Applied Physics, 1992, 72, 2857-2872.	1.1	56
238	Midgap states in a-Si:H and a-SiGe:H p-i-n solar cells and Schottky junctions by capacitance techniques. Journal of Applied Physics, 1992, 71, 5941-5951.	1.1	79
239	The bonded unipolar silicon-silicon junction. Journal of Applied Physics, 1992, 72, 124-140.	1.1	40
240	Gap states in hydrogenated microcrystalline silicon grown by glow discharge technique. Journal of Applied Physics, 1992, 72, 2923-2926.	1.1	3
241	SOLAR CELLS ON THE BASIS OF THIN POLYCRYSTALLINE CdSe FILMS: INVESTIGATIONS OF MIS AND PN HETEROSTRUCTURES. International Journal of Solar Energy, 1992, 13, 19-23.	0.2	1
242	Configurational Relaxation of the D Defect in Hydrogenated Amorphous Silicon as a Function of Fermi Energy. Materials Research Society Symposia Proceedings, 1992, 258, 211.	0.1	0
243	An Assessment of the Light Modulated Photocurrent Method in the Study of the Density of Gap States in Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1992, 258, 813.	0.1	16
244	An Investigation of a-Si:H Thin Film Transistors by A Comparison of Transient Measurements and Numerical Simulations.. Materials Research Society Symposia Proceedings, 1992, 258, 985.	0.1	2
245	Lock-in rate-window thermomodulation (thermal wave) and photomodulation spectrometry. Review of Scientific Instruments, 1992, 63, 2977-2988.	0.6	16
246	Review of direct measurements of mobility gaps in a-Si:H using internal photoemission. Journal of Non-Crystalline Solids, 1992, 141, 16-23.	1.5	14
247	Deep defect structure and carrier dynamics in amorphous silicon and silicon-germanium alloys determined by transient photocapacitance methods. Journal of Non-Crystalline Solids, 1992, 141, 142-154.	1.5	39
248	Light-induced defects in phosphorus-doped hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1992, 141, 176-187.	1.5	4
249	Density of states of inhomogeneous hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1992, 143, 241-245.	1.5	1
250	Charge transport in a-Si: H PIN solar cells under AC excitation. Solar Energy Materials and Solar Cells, 1992, 27, 69-77.	3.0	1
251	Characterization of a-Si:H and a-SiGe:H p-i-n and Schottky junctions by admittance circuit modeling. IEEE Transactions on Electron Devices, 1992, 39, 2368-2376.	1.6	10
252	Depth profiling of defects in a-Si:H films by means of modulated photocurrent. Solid State Communications, 1993, 86, 277-280.	0.9	2
253	DLTS evaluation of nonexponential transients of defect levels in cuprous oxide (Cu ₂ O). Solid-State Electronics, 1993, 36, 431-434.	0.8	17
254	Interface state density of SiN _x :H/c-Si MIS structure. Journal of Non-Crystalline Solids, 1993, 164-166, 849-852.	1.5	4

#	ARTICLE	IF	CITATIONS
255	Substrate disorder induced by a surface chemical reaction: the fluorine-silicon interaction. Surface Science, 1993, 292, 171-181.	0.8	20
256	XeF ₂ etching of Si(111): The geometric structure of the reaction layer. Physical Review B, 1993, 47, 15648-15659.	1.1	60
257	Defect chemical potential and the density of states in amorphous silicon. Physical Review Letters, 1993, 70, 1654-1657.	2.9	33
258	Improved defect-pool model for charged defects in amorphous silicon. Physical Review B, 1993, 48, 10815-10827.	1.1	279
259	Charge redistribution process on gap states in hydrogenated amorphous silicon. Physical Review Letters, 1993, 71, 2979-2982.	2.9	11
260	Dangling-bond relaxation and deep-level measurements in hydrogenated amorphous silicon. Physical Review B, 1993, 48, 8667-8671.	1.1	45
261	Measured and calculated distributions of deep defect states in hydrogenated amorphous silicon: Verification of deep defect relaxation dynamics. Physical Review Letters, 1993, 71, 597-600.	2.9	36
262	Defect Relaxation Dynamics in Amorphous Silicon. Materials Research Society Symposia Proceedings, 1993, 297, 183.	0.1	4
263	Doping Efficiency of N-Type a-Si:H Doped with a Liquid Organic Source. Materials Research Society Symposia Proceedings, 1993, 297, 503.	0.1	0
264	Conduction and Valence Band Offsets at the Hydrogenated Amorphous Silicon-Carbon/Crystalline Silicon Interface Via Capacitance Techniques. Materials Research Society Symposia Proceedings, 1993, 297, 705.	0.1	3
265	Subthreshold Characteristics and Interface State Density of a-Si:H TFT. Materials Research Society Symposia Proceedings, 1993, 297, 889.	0.1	6
266	Novel Structure for Measuring the Density-of-State Distribution of High-Resistivity Semiconductor Films by Isothermal Capacitance Transient Spectroscopy. Japanese Journal of Applied Physics, 1994, 33, 6727-6732.	0.8	7
267	Effect of carbon impurities on the density of states and the stability of hydrogenated amorphous silicon. Physical Review B, 1994, 50, 16985-16994.	1.1	25
268	Depletion layer width in undoped a-Si:H Schottky barrier revealed by reverse bias photocurrent. Journal of Applied Physics, 1994, 75, 3522-3529.	1.1	6
269	Exploration of Defect Relaxation Dynamics in Hydrogenated Amorphous Silicon using Temperature Switching Experiments. Materials Research Society Symposia Proceedings, 1994, 336, 207.	0.1	1
270	Charge and Current Transient Measurements on N-Type Hydrogenated Amorphous Silicon in the Relaxation Regime. Materials Research Society Symposia Proceedings, 1994, 336, 455.	0.1	3
271	Density of Deep Bandgap States in Amorphous Silicon From the Temperature Dependence of Thin Film Transistor Current. Materials Research Society Symposia Proceedings, 1994, 336, 823.	0.1	43
272	Characterization of Localized Density of States in Intrinsic a-Si and poly-Si Films by Transient Voltage Spectroscopy. Materials Research Society Symposia Proceedings, 1995, 377, 215.	0.1	0

#	ARTICLE	IF	CITATIONS
273	The Role of Deep Defect Relaxation Dynamics in Optical Processes in Hydrogenated Amorphous Silicon. Materials Research Society Symposia Proceedings, 1995, 377, 221.	0.1	1
274	A realistic trap distribution model for numerical simulation of amorphous silicon thin-film transistors and phototransistors. IEEE Transactions on Electron Devices, 1995, 42, 1333-1339.	1.6	3
275	Theory of non-steady-state electrical characteristics of metal-insulator-metal structures with Schottky barriers and uniformly distributed interface impurity states. Solid-State Electronics, 1995, 38, 619-625.	0.8	2
276	Bandgap engineering of amorphous semiconductors for solar cell applications. Progress in Photovoltaics: Research and Applications, 1995, 3, 149-176.	4.4	24
277	Physical properties of a-Si:H based compositional periodic multilayers. Physical Review B, 1995, 52, 8829-8847.	1.1	17
278	Electron emission from deep states and evaluation of the density of states in a-Si:H. Journal of Applied Physics, 1995, 77, 5661-5668.	1.1	22
279	Rapid determination of a-Si:H gap states by double-beam photocapacitance. Semiconductor Science and Technology, 1995, 10, 1353-1361.	1.0	1
280	Temperature dependence of the capture cross section determined by DLTS on an MOS structure. Semiconductor Science and Technology, 1995, 10, 1510-1519.	1.0	20
281	On thermal quenching of the photoconductivity in hydrogenated amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1995, 72, 35-66.	0.6	56
282	Fluctuation tail of valence bands in hydrogenated amorphous silicon. Physical Review B, 1995, 52, 10979-10992.	1.1	15
283	Internal photoemission on a-Si:H Schottky barrier structures revisited. Journal of Non-Crystalline Solids, 1995, 190, 58-66.	1.5	24
284	Transient modulated photocurrent studies in hydrogenated amorphous silicon: a new look at defect relaxation dynamics. Journal of Non-Crystalline Solids, 1995, 190, 123-132.	1.5	10
285	Determination of gap states density in PECVD a-Si:H from amorphous-crystalline heterojunctions. , 0, , .		1
286	Bias light induced defect relaxation phenomena in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1996, 198-200, 512-516.	1.5	3
287	Defect Characterization of High-Rate Deposited Hydrogenated Amorphous Silicon Films. Materials Research Society Symposia Proceedings, 1996, 420, 599.	0.1	0
288	Localized density of states in hydrogenated amorphous silicon/silicon nitride interfaces studied by transient voltage spectroscopy. Journal of Applied Physics, 1996, 80, 5786-5790.	1.1	4
289	New approach to bias scan DLTS for rapid evaluation of interface states in MOS structures. Solid-State Electronics, 1996, 39, 1507-1514.	0.8	3
290	Conduction- and valence-band offsets at the hydrogenated amorphous silicon-carbon/crystalline silicon interface via capacitance techniques. Physical Review B, 1996, 54, 4885-4890.	1.1	27

#	ARTICLE	IF	CITATIONS
291	Analysis of post-transit photocurrents and electroluminescence spectra from a-Si:H solar cells. Journal of Applied Physics, 1996, 79, 3597-3602.	1.1	16
292	A Simple Graphical Method for Evaluating the Polarization and Relaxation Times of Dipoles or Densities and Energy Levels of Traps in a Dielectric Film from Transient Discharge Current. Japanese Journal of Applied Physics, 1997, 36, 3569-3575.	0.8	5
293	An Approach to Study Band-gap and Interface States in a-Si:H p-i-n Solar Cells. Japanese Journal of Applied Physics, 1997, 36, 6687-6693.	0.8	4
294	Small-signal analysis of semiconductor heterojunctions with interacting interface states. Semiconductor Science and Technology, 1997, 12, 1217-1225.	1.0	2
295	The thermal equilibrium changes on reverse bias annealing in Schottky diodes. Semiconductor Science and Technology, 1997, 12, 1451-1454.	1.0	1
296	Evidence for the Improved Defect-Pool Model for Gap States in Amorphous Silicon from Charge DLTS Experiments on Undoped a-Si:H. Physical Review Letters, 1997, 78, 1102-1105.	2.9	55
297	Characterization of a-Si:H based metal/insulator/semiconductor structures by feedback charge capacitance-voltage measurements and charge deep-level transient spectroscopy. Journal of Applied Physics, 1997, 82, 4372-4377.	1.1	8
298	Transient photoconductivity with optical bias in undoped and slightly n-doped hydrogenated amorphous silicon. Physical Review B, 1997, 55, 10528-10540.	1.1	1
299	Electrical properties of PECVD amorphous silicon-carbon alloys from amorphous-crystalline heterojunctions. Diamond and Related Materials, 1997, 6, 1555-1558.	1.8	7
300	Ohmic and space-charge limited conduction in cobalt phthalocyanine thin films. Thin Solid Films, 1997, 305, 336-340.	0.8	39
301	A Generalized Theory of Electrical Characteristics of Schottky Barriers for Amorphous Materials. Physica Status Solidi A, 1997, 164, 733-745.	1.7	3
302	New experimental facts on the Staebler-Wronski effect. Journal of Non-Crystalline Solids, 1998, 227-230, 316-319.	1.5	11
303	Identification of the dominant electron deep trap in amorphous silicon from ESR and modulated photocurrent measurements: implications for defect models. Journal of Non-Crystalline Solids, 1998, 227-230, 348-352.	1.5	14
304	Band gap states in a-SiGe:H alloys determined from charge DLTS experiments. , 0, , .		0
305	Electrode interdependence and hole capacitance in capacitance-voltage characteristics of hydrogenated amorphous silicon thin-film transistor. Journal of Applied Physics, 1998, 83, 8051-8056.	1.1	17
306	Compensating levels in p-type ZnSe:N studied by optical deep-level transient spectroscopy. Physical Review B, 1998, 58, 10502-10509.	1.1	3
307	Electrode Interdependence and Hole Capacitance in the Capacitance-Voltage Characteristics of Hydrogenated Amorphous Silicon Thin-Film Transistors. Materials Research Society Symposia Proceedings, 1998, 507, 67.	0.1	0
308	Characterization of Tetrahedrally Bonded Amorphous Carbon Via Capacitance Techniques. Materials Research Society Symposia Proceedings, 1998, 508, 197.	0.1	0

#	ARTICLE	IF	CITATIONS
309	Characterization of Tetrahedrally Bonded Amorphous Carbon Via Capacitance Techniques. Materials Research Society Symposia Proceedings, 1998, 509, 119.	0.1	0
310	Very low densities of localized states at the Fermi level in hydrogenated polymorphous silicon from capacitance and space-charge-limited current measurements. Applied Physics Letters, 1999, 75, 3351-3353.	1.5	55
311	Defect densities in tetrahedrally bonded amorphous carbon deduced by junction capacitance techniques. Applied Physics Letters, 1999, 74, 371-373.	1.5	11
312	Capacitance and Transient Photocapacitance Studies of Tetrahedral Amorphous Carbon. Materials Research Society Symposia Proceedings, 2000, 621, 661.	0.1	0
313	Low-energy argon ion beam treatment of a-Si:H/Si structure. Applied Surface Science, 2000, 166, 61-66.	3.1	1
314	Investigation of Transient Reverse Currents in X-Ray Detector Pin Diodes by Discharge Current Transient Spectroscopy. Japanese Journal of Applied Physics, 2000, 39, 178-179.	0.8	6
315	Experimental evidence for complementary spatial sensitivities of capacitance and charge deep-level transient spectroscopies. Semiconductor Science and Technology, 2000, 15, 378-385.	1.0	5
316	Ferroelectricity and electronic defect characteristics of c-oriented Sr _{0.25} Ba _{0.75} Nb ₂ O ₆ thin films deposited on Si substrates. Applied Physics Letters, 2000, 76, 3472-3474.	1.5	25
317	Observation of a band of fast responding metastable deep traps for charge carriers in crystalline Si(n)/SiN _x :H/amorphous Si:H/Al structures. Journal of Non-Crystalline Solids, 2000, 277, 207-218.	1.5	1
318	Generation-recombination noise studied in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 2000, 266-269, 232-236.	1.5	8
319	Defect band distributions in hydrogenated tetrahedral amorphous carbon/crystalline silicon heterostructures. Journal of Non-Crystalline Solids, 2000, 266-269, 1077-1081.	1.5	4
320	Effects of light soaking on amorphous silicon. , 0, ,		1
321	Material Properties of Hydrogenated Amorphous Silicon. , 0, , 541-595.		0
322	Amorphous silicon (a-Si) electrical conductivity. , 0, , 1-2.		0
323	Instability evolution within a-SiN _x film assessed through MIS structure under bias and temperature stresses. Journal of Non-Crystalline Solids, 2001, 296, 27-38.	1.5	7
324	Electronic properties of hydrogenated amorphous carbon films deposited using ECR-RF plasma method. Diamond and Related Materials, 2001, 10, 200-206.	1.8	23
325	Density of gap states in amorphous hydrogenated silicon carbide determined using high-frequency capacitance-voltage measurement technique. Diamond and Related Materials, 2001, 10, 1273-1277.	1.8	4
326	Characterization of the hole capacitance of hydrogenated amorphous silicon metal-insulator-semiconductor structures. Journal of Applied Physics, 2001, 90, 6226-6229.	1.1	2

#	ARTICLE	IF	CITATIONS
327	Correlation between the results of charge deep-level transient spectroscopy and ESR techniques for undoped hydrogenated amorphous silicon. <i>Physical Review B</i> , 2002, 66, .	1.1	18
328	Reverse bias annealing of Schottky diodes: evidence for the lower defect density and better stability of polymorphous silicon compared to amorphous silicon. <i>Journal of Non-Crystalline Solids</i> , 2002, 299-302, 599-604.	1.5	9
329	Photocurrent spectroscopy of thin passive films. , 2002, , 373-414.		14
330	Defects induced in amorphous silicon thin films by light soaking. <i>Thin Solid Films</i> , 2002, 403-404, 513-516.	0.8	3
331	UV light induced defects in amorphous silicon thin films. <i>Vacuum</i> , 2003, 71, 135-139.	1.6	5
332	Study on variable capacitance diode of (p)nc-Si:H/(n)c-Si heterojunction. <i>Vacuum</i> , 2003, 71, 465-469.	1.6	6
333	Capacitance techniques for the evaluation of electronic properties and defects in disordered thin film semiconductors. <i>Thin Solid Films</i> , 2003, 427, 127-132.	0.8	12
334	Charge-based deep level transient spectroscopy of phosphorous-doped homoepitaxial diamond. <i>Journal of Applied Physics</i> , 2003, 94, 5832-5843.	1.1	8
335	Slow relaxation of polar impurities in amorphous carbon thin films through capacitive spectroscopy. <i>Journal of Applied Physics</i> , 2003, 93, 9953-9960.	1.1	3
337	Evolution of Charged Gap States in a-Si:H Under Light Exposure. <i>Materials Research Society Symposia Proceedings</i> , 2003, 762, 1261.	0.1	2
338	Origin of charged gap states in a-Si:H and their evolution during light soaking. <i>Physical Review B</i> , 2004, 69, .	1.1	35
339	Method for the determination of the capture cross sections of electrons from space-charge-limited conduction in the dark and under illumination in amorphous semiconductors. <i>Applied Physics Letters</i> , 2004, 85, 245-247.	1.5	10
340	Investigation of a-Si:H/c-Si heterojunction solar cells interface properties. <i>Thin Solid Films</i> , 2004, 451-452, 345-349.	0.8	21
341	Determination of electrical conduction mechanism and optical band gap of a new charge transfer complex: TCNQ-PANT. <i>Solid State Communications</i> , 2004, 132, 229-234.	0.9	73
342	Semiconductor electrochemistry approach to passivity and passivity breakdown of metals and metallic alloys. <i>Corrosion Engineering Science and Technology</i> , 2004, 39, 71-81.	0.7	36
343	Unusual properties of C-T characteristics of hydrogen implanted and annealed Si. <i>EPJ Applied Physics</i> , 2004, 27, 141-144.	0.3	0
344	Microstructural relaxation of hydrogenated amorphous carbon thin films. <i>Thin Solid Films</i> , 2005, 482, 90-93.	0.8	1
345	Characterization of an a-Si:H/c-Si interface by admittance spectroscopy. <i>Semiconductors</i> , 2005, 39, 904-909.	0.2	10

#	ARTICLE	IF	CITATIONS
346	The determination of carrier mobilities in CIGS photovoltaic devices using high-frequency admittance measurements. <i>Thin Solid Films</i> , 2005, 480-481, 336-340.	0.8	80
347	Hopping Transport of Electrons and Holes at Localized Band Tail States in Amorphous Hydrogenated Silicon and Amorphous Heavy-Hydrogenated Silicon. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 4764-4769.	0.8	9
348	Determination of semiconductor band gap state parameters from photoconductivity measurements. II. Experimental results. <i>Physical Review B</i> , 2006, 73, .	1.1	25
349	Defect-state engineering in a-Si:H: An effective tool for studying processes during light-induced degradation. <i>Journal of Non-Crystalline Solids</i> , 2006, 352, 1059-1063.	1.5	2
350	Interface properties of a-Si:H/c-Si heterojunction solar cells from admittance spectroscopy. <i>Thin Solid Films</i> , 2006, 511-512, 385-389.	0.8	42
351	Analysis of structure and defects in thin silicon films deposited from hydrogen diluted silane. <i>Thin Solid Films</i> , 2006, 511-512, 252-257.	0.8	26
352	Determination of Density of States in Amorphous Carbon. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 1775-1781.	1.6	4
353	Tunnelling in heterojunction of n-type hydrogenated nanocrystalline silicon film with p+-type crystal silicon. <i>Semiconductor Science and Technology</i> , 2006, 21, 532-539.	1.0	7
354	Conduction behaviour of hydrogenated nanocrystalline silicon backward diode. <i>Nanotechnology</i> , 2007, 18, 025203.	1.3	6
355	Time evolution of charged defect states in tritiated amorphous silicon. <i>Journal of Applied Physics</i> , 2007, 102, 103715.	1.1	0
356	Electronic characteristics of n-type nanocrystalline/p-type crystalline silicon heterostructure. <i>Semiconductor Science and Technology</i> , 2007, 22, 601-607.	1.0	1
357	Investigation on high mobility nanocrystalline Si with crystalline Si heterostructure. <i>Superlattices and Microstructures</i> , 2007, 41, 216-226.	1.4	2
358	Carrier conduction in heterojunction of hydrogenated nanocrystalline silicon with crystal silicon. <i>Thin Solid Films</i> , 2007, 515, 3997-4003.	0.8	2
359	Oscillator strength reduction induced by external electric fields in self-assembled quantum dots and rings. <i>Physical Review B</i> , 2007, 75, .	1.1	60
360	Electron hopping randomwalk at localized band tail states with exponential density in amorphous hydrogenated silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 777-781.	0.8	2
361	Spectral response characterization of a-Si:H-based MIS-type photosensors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3410-3413.	0.8	4
362	Junction capacitance study of an oxygen impurity defect exhibiting configuration relaxation in amorphous silicon-germanium alloys deposited by hot-wire CVD. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 2126-2130.	1.5	4
363	Characterization of amorphous/crystalline silicon interfaces from electrical measurements. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1066, 1.	0.1	5

#	ARTICLE	IF	CITATIONS
364	The role of bulk and interface states on performance of a-Si:H p-i-n solar cells using reverse current-voltage technique. Journal Physics D: Applied Physics, 2009, 42, 145115.	1.3	3
365	Insights and challenges toward understanding the electronic properties of hydrogenated nanocrystalline silicon. Philosophical Magazine, 2009, 89, 2541-2555.	0.7	2
366	Effects of the PEDOT interface states distribution in polymeric OLEDs. , 2009, , .		0
367	III-phosphides heterojunction solar cell interface properties from admittance spectroscopy. Journal Physics D: Applied Physics, 2009, 42, 165307.	1.3	10
368	Discussion of some "trap signatures" observed by admittance spectroscopy in CdTe thin-film solar cells. Journal of Applied Physics, 2010, 108, .	1.1	24
369	A critical assessment of the Mott-Schottky analysis for the characterisation of passive film-electrolyte junctions. Russian Journal of Electrochemistry, 2010, 46, 1306-1322.	0.3	61
370	Simulation of hetero-junction silicon solar cells with AMPS-1D. Solar Energy Materials and Solar Cells, 2010, 94, 62-67.	3.0	122
371	Hopping Conduction Observed in Thermal Admittance Spectroscopy. Physical Review Letters, 2010, 104, 226403.	2.9	43
372	Physicochemical Characterization of Thermally Aged Anodic Films on Magnetron-Sputtered Niobium. Journal of the Electrochemical Society, 2010, 157, C258.	1.3	22
373	Structural and electronic properties of hydrogenated polymorphous silicon films deposited at high rate. Journal of Applied Physics, 2011, 109, 023713.	1.1	17
375	Effects of the PEDOT interface trap distribution in polymeric OLEDs. Organic Electronics, 2011, 12, 1159-1165.	1.4	12
376	High deposition rate hydrogenated polymorphous silicon characterized by different capacitance techniques. Thin Solid Films, 2011, 519, 5364-5370.	0.8	4
377	Characterization of defects in hydrogenated amorphous silicon deposited on different substrates by capacitance techniques. Thin Solid Films, 2011, 519, 5473-5480.	0.8	2
378	Admittance spectroscopy of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) based organic light emitting diodes. Journal of Applied Physics, 2011, 109, 114504.	1.1	5
379	Identification of defect types in moderately Si-doped GaInNAsSb layer in p-GaAs/n-GaInNAsSb/n-GaAs solar cell structure using admittance spectroscopy. Journal of Applied Physics, 2012, 112, .	1.1	13
380	Capacitance-Voltage Measurement With Photon Probe to Quantify the Trap Density of States in Amorphous Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 1015-1017.	2.2	15
381	Space charge capacitance spectroscopy in amorphous silicon Schottky diodes: Theory, modeling, and experiments. Journal of Non-Crystalline Solids, 2012, 358, 2007-2010.	1.5	1
382	Density of states evaluations from oscillating/moving grating techniques. Journal of Non-Crystalline Solids, 2012, 358, 2031-2034.	1.5	5

#	ARTICLE	IF	CITATIONS
383	Dynamic Response of Thin-Film Semiconductors to AC Voltage Perturbations. ChemPhysChem, 2012, 13, 2910-2918.	1.0	8
384	Mechanism of Trapping Effect in Heterojunction With Intrinsic Thin-Layer Solar Cells: Effect of Density of Defect States. IEEE Transactions on Electron Devices, 2012, 59, 1227-1235.	1.6	22
385	The identification, characterization and mitigation of defect states in organic photovoltaic devices: a review and outlook. Energy and Environmental Science, 2013, 6, 3414.	15.6	124
386	Tunnel injection and power efficiency of InGaN/GaN light-emitting diodes. Semiconductors, 2013, 47, 127-134.	0.2	13
387	Study of the properties of solar cells based on a-Si:H p-i-n structures by admittance spectroscopy. Semiconductors, 2013, 47, 1090-1096.	0.2	3
388	Carrier emission from defects in intrinsic hydrogenated amorphous silicon studied by junction-capacitance methods. Journal of Non-Crystalline Solids, 2013, 381, 35-39.	1.5	1
389	Characterization of space charge layer deep defects in n ⁺ -CdS/p-CdTe solar cells by temperature dependent capacitance spectroscopy. Journal of Applied Physics, 2013, 113, .	1.1	16
390	Characterization of bulk defect response in Cu(In, Ga)Se ₂ thin-film solar cell using DLTS. , 2013, , .		0
391	Microstructure Characterization of Amorphous Silicon Films by Effusion Measurements of Implanted Helium. Materials Research Society Symposia Proceedings, 2013, 1536, 175-180.	0.1	3
392	Forward bias capacitance spectroscopy for characterization of semiconductor junctions: Application to a-Si:H p-i-n diode. Applied Physics Letters, 2013, 102, 153504.	1.5	3
393	Response to "Comment on "On accurate capacitance characterization of organic photovoltaic cells" [Appl. Phys. Lett. 102, 076101 (2013)]. Applied Physics Letters, 2013, 102, 076102.	1.5	0
394	Deep-level transient spectroscopy of Al/a-Si:H/c-Si structures for heterojunction solar cell applications. Journal of Applied Physics, 2014, 116, .	1.1	10
395	Characterization of the Manufacturing Processes to Grow Triple-Junction Solar Cells. International Journal of Photoenergy, 2014, 2014, 1-10.	1.4	13
396	In-situ characterization of trapped charges in amorphous semiconductor films during plasma-enhanced chemical vapor deposition. AIP Advances, 2014, 4, .	0.6	11
397	Deep-level transient spectroscopy on an amorphous InGaZnO ₄ Schottky diode. Applied Physics Letters, 2014, 104, 082112.	1.5	24
398	Applications of real-time and mapping spectroscopic ellipsometry for process development and optimization in hydrogenated silicon thin-film photovoltaics technology. Solar Energy Materials and Solar Cells, 2014, 129, 32-56.	3.0	19
399	Evaluation of the characteristic curves of a-Si:H based devices with the Simmons-Taylor approximation when the defect pool model is used. Physica Status Solidi (B): Basic Research, 2015, 252, 170-180.	0.7	7
400	Assessment on the use of the amorphous semiconductor theory for the analysis of oxide films. Electrochimica Acta, 2015, 179, 460-468.	2.6	5

#	ARTICLE	IF	CITATIONS
401	Revisiting the theory and usage of junction capacitance: Application to high efficiency amorphous/crystalline silicon heterojunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2015, 135, 8-16.	3.0	21
402	Laplace deep level transient spectroscopy study of intrinsic hydrogenated amorphous silicon. <i>Journal of Non-Crystalline Solids</i> , 2015, 411, 119-124.	1.5	2
403	Characterization of transport properties of organic semiconductors using impedance spectroscopy. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 4463-4474.	1.1	17
404	Light-induced metastable defects in a-Se ₉₀ X ₁₀ (X = Sb, In and Ag) thin films. <i>Phase Transitions</i> , 2015, 88, 939-949.	0.6	5
405	Comparison and interpretation of admittance spectroscopy and deep level transient spectroscopy from co-evaporated and solution-deposited Cu ₂ ZnSn(S _x) Tj ETQq0 0 0 rgBT /Overdock 10 Tf		
406	Defects in solution-processed dithienylsilole-based small-molecule photovoltaic thin-films. <i>Journal of Applied Physics</i> , 2016, 119, 025501.	1.1	7
408	Impact of band tail distribution on carrier trapping in hydrogenated amorphous silicon for solar cell applications. <i>Journal of Non-Crystalline Solids</i> , 2016, 436, 44-50.	1.5	16
409	A new method for unambiguous determination of trap parameters from afterglow and TSL curves connection: Example on garnets. <i>Optical Materials</i> , 2017, 72, 161-168.	1.7	14
410	Hopping conductivity and dielectric relaxation in Schottky barriers on GaN. <i>Semiconductors</i> , 2017, 51, 1186-1193.	0.2	10
411	The Amorphous Semiconductor Schottky Barrier Approach to Study the Electronic Properties of Anodic Films on Ti. <i>Journal of the Electrochemical Society</i> , 2017, 164, C516-C525.	1.3	17
412	Differential Capacitance Measurements on Passive Films. , 2018, , 75-92.		2
413	Dry Passivation Process for Silicon Heterojunction Solar Cells Using Hydrogen Plasma Treatment Followed by <i>In Situ</i> a-Si:H Deposition. <i>IEEE Journal of Photovoltaics</i> , 2018, 8, 1539-1545.	1.5	15
414	Plasma-Induced Electronic Defects: Generation and Annihilation Kinetics in Hydrogenated Amorphous Silicon. <i>Physical Review Applied</i> , 2018, 10, .	1.5	30
415	Modeling Gain Mechanisms in Amorphous Silicon Due to Efficient Carrier Multiplication and Trap-Induced Junction Modulation. <i>Journal of Lightwave Technology</i> , 2019, 37, 5056-5066.	2.7	3
416	Recent Progress in Understanding the Properties of the Amorphous Silicon/Crystalline Silicon Interface. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800877.	0.8	3
417	Hydrogenated amorphous silicon characterization from steady state photoconductive measurements. <i>Semiconductor Science and Technology</i> , 2019, 34, 045010.	1.0	4
418	Interface Properties of GaP/Si Heterojunction Fabricated by PEALD. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800617.	0.8	8
419	A Deep Level Transient Spectroscopy Study of Hole Traps in GexSe1-x-based Layers for Ovonic Threshold Switching Selectors. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 044006.	0.9	0

#	ARTICLE	IF	CITATIONS
421	Local Structure, Thermal, Optical and Electrical Properties of LiFePO ₄ Polycrystalline Synthesized by Co-Precipitation Method. Brazilian Journal of Physics, 2021, 51, 1521-1528.	0.7	4
422	Effect of air mass on carrier losses in bifacial silicon heterojunction solar cells. Solar Energy Materials and Solar Cells, 2021, 230, 111293.	3.0	8
423	Fundamental and applied work on glow discharge material. , 1984, , 63-118.		17
424	Solar energy conversion. , 1984, , 203-244.		6
425	Recent advances. Topics in Applied Physics, 1979, , 331-343.	0.4	12
426	Theory of electronic structure. Topics in Applied Physics, 1984, , 5-60.	0.4	21
427	The spectroscopy of localized states. Topics in Applied Physics, 1984, , 195-259.	0.4	23
428	Time-resolved charge transport in hydrogenated amorphous silicon. Topics in Applied Physics, 1984, , 261-300.	0.4	42
429	Density of Gap States in Undoped and Doped Amorphous Hydrogenated Silicon Obtained by Optical Spectroscopy. , 1987, , 459-468.		5
430	Optical, Electronic and Structural Properties. , 1998, , 41-68.		2
431	Density of States in Noncrystalline Solids. , 1985, , 313-341.		5
432	Chemistry and Physics of Covalent Amorphous Semiconductors. , 1985, , 5-103.		28
434	Amorphous-Crystalline Heterojunctions. , 1985, , 483-500.		5
436	Electronic Transport Properties of High Deposition Rate a-Si:H Material. , 1991, , 375-378.		2
437	Propriétés électroniques et schémas de bandes dans les semi-conducteurs amorphes. I. Concepts fondamentaux. Annales De Physique, 1991, 16, 261-304.	0.2	6
438	Defects. Advances in Condensed Matter Science, 2003, , 158-202.	0.3	2
439	Characteristics of Grain Boundaries in Polycrystalline Si Films fabricated by Chemical Vapor Deposition and Subsequent Annealing. IEEJ Transactions on Sensors and Micromachines, 2004, 124, 14-20.	0.0	0
440	PECCS Measurements in Oxide FETs. SpringerBriefs in Physics, 2013, , 59-81.	0.2	0

#	ARTICLE	IF	CITATIONS
441	Instrumentations for PECCS. SpringerBriefs in Physics, 2013, , 17-29.	0.2	0
444	Schottky Barriers on Amorphous Si and Their Applications. , 1984, , 335-366.		1
445	Bonding at Bulk and Defect Sites in Amorphous Semiconductors. , 1984, , 279-282.		0
446	Defects in Amorphous Semiconductors. , 1985, , 521-531.		0
447	Is the DLTS Density of States for Amorphous Silicon Correct?. , 1985, , 299-314.		1
448	Doping Effects in Amorphous Silicon. , 1985, , 845-850.		0
450	Theoretical Calculations of the Electronic Structure in the Si-SiO ₂ Systems. , 1988, , 259-269.		0
453	Influence of the RF Power Density on the Electrical Properties of Glow-Discharge Amorphous Silicon. , 1991, , 368-370.		0
454	Impact of Ag content on the light induced defects of Se-In thin films and their suitability for optoelectronic devices. AIP Conference Proceedings, 2020, , .	0.3	0
455	Measurement methods, part B. , 0, , 1-12.		0
456	Measurement methods, part D. , 0, , 1-10.		0
457	Amorphous silicon (a-Si) figures to electrical conductivity. , 0, , 1-32.		0
458	Amorphous silicon (a-Si) density of localized gap states. , 0, , 1-2.		0
459	Amorphous silicon (a-Si) figures to density of localized gap states. , 0, , 1-6.		0
460	Material Properties of Hydrogenated Amorphous Silicon. , 0, , 541-595.		0